

Hisashi Masui

List of Publications by Year in descending order

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44
papers

1,747
citations

304743

22
h-index

289244

40
g-index

44
all docs

44
docs citations

44
times ranked

1283
citing authors

#	ARTICLE	IF	CITATIONS
1	High Power and High External Efficiency m-Plane InGaN Light Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, L126-L128.	1.5	241
2	Nonpolar and Semipolar III-Nitride Light-Emitting Diodes: Achievements and Challenges. IEEE Transactions on Electron Devices, 2010, 57, 88-100.	3.0	230
3	Optical properties of yellow light-emitting diodes grown on semipolar (112 $\bar{2}$) bulk GaN substrates. Applied Physics Letters, 2008, 92, .	3.3	167
4	A yellow-emitting Ce ³⁺ phosphor, La ^{1-x} Ce ^x Sr ₂ AlO ₅ , for white light-emitting diodes. Applied Physics Letters, 2008, 93, .	3.3	158
5	Polarized Light Emission from Nonpolar InGaN Light-Emitting Diodes Grown on a Bulk m-Plane GaN Substrate. Japanese Journal of Applied Physics, 2005, 44, L1329-L1332.	1.5	68
6	Nonpolar m-Plane Blue-Light-Emitting Diode Lamps with Output Power of 23.5 mW under Pulsed Operation. Japanese Journal of Applied Physics, 2006, 45, 739-741.	1.5	68
7	Optical polarization characteristics of m-oriented InGaN/GaN light-emitting diodes with various indium compositions in single-quantum-well structure. Journal Physics D: Applied Physics, 2008, 41, 225104.	2.8	57
8	Quantum-confined Stark effect on photoluminescence and electroluminescence characteristics of InGaN-based light-emitting diodes. Journal Physics D: Applied Physics, 2008, 41, 165105.	2.8	55
9	Compositional Dependence of Nonpolar m-Plane In _x Ga _{1-x} N/GaN Light Emitting Diodes. Applied Physics Express, 0, 1, 041101.	2.4	53
10	Light-polarization characteristics of electroluminescence from InGaN-GaN light-emitting diodes prepared on (112 $\bar{2}$)-plane GaN. Journal of Applied Physics, 2006, 100, 113109.	2.5	46
11	Comparison of InGaN/GaN light emitting diodes grown on m-plane and a-plane bulk GaN substrates. Physica Status Solidi - Rapid Research Letters, 2008, 2, 89-91.	2.4	46
12	Effects of piezoelectric fields on optoelectronic properties of InGaN/GaN quantum-well light-emitting diodes prepared on nonpolar (1 $\bar{1}00$) and semipolar (1 $\bar{1}00$) orientations. Journal Physics D: Applied Physics, 2009, 42, 135106.	2.4	46
13	Optical polarization characteristics of InGaN-GaN light-emitting diodes fabricated on GaN substrates oriented between (101 \bar{A}) and (101 \bar{A} -1 \bar{A}) planes. Applied Physics Letters, 2008, 92, .	3.3	34
14	Hexagonal pyramid shaped light-emitting diodes based on ZnO and GaN direct wafer bonding. Applied Physics Letters, 2006, 89, 171116.	3.3	32
15	Luminescence Characteristics of N-Polar GaN and InGaN Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 071003.	1.5	31
16	Highly efficient broad-area blue and white light-emitting diodes on bulk GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 200-202.	1.8	29
17	First-Moment Analysis of Polarized Light Emission from InGaN/GaN Light-Emitting Diodes Prepared on Semipolar Planes. Japanese Journal of Applied Physics, 2006, 45, L904-L906.	1.5	28
18	Increased Polarization Ratio on Semipolar (112 $\bar{2}$) InGaN/GaN Light-Emitting Diodes with Increasing Indium Composition. Japanese Journal of Applied Physics, 2008, 47, 7854.	1.5	28

#	ARTICLE	IF	CITATIONS
19	Photoelectrochemical Properties of Nonpolar and Semipolar GaN. Japanese Journal of Applied Physics, 2007, 46, 6573-6578.	1.5	27
20	Correlation between Optical Polarization and Luminescence Morphology of (11̄22)-Oriented InGaN/GaN Quantum-Well Structures. Applied Physics Express, 0, 2, 071002.	2.4	27
21	Optical polarization of <i>m</i> -plane InGaN/GaN light-emitting diodes characterized via confocal microscope. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1203-1206.	1.8	25
22	Effects of off-axis GaN substrates on optical properties of <i>m</i> -plane InGaN/GaN light-emitting diodes. Journal of Crystal Growth, 2008, 310, 4968-4971.	1.5	25
23	Nonpolar-oriented InGaN light-emitting diodes for liquid-crystal display backlighting. Journal of the Society for Information Display, 2008, 16, 571-578.	2.1	25
24	Technique to evaluate the diode ideality factor of light-emitting diodes. Applied Physics Letters, 2010, 96, 073509.	3.3	25
25	Milliwatt Power Deep Ultraviolet Light Emitting Diodes Grown on Silicon Carbide. Japanese Journal of Applied Physics, 2005, 44, L502-L504.	1.5	23
26	Geometrical Characteristics and Surface Polarity of Inclined Crystallographic Planes of the Wurtzite and Zinblende Structures. Journal of Electronic Materials, 2009, 38, 756-760.	2.2	21
27	Electroluminescence efficiency of (1,0,̄1,0)-oriented InGaN-based light-emitting diodes at low temperature. Journal Physics D: Applied Physics, 2008, 41, 082001.	2.8	18
28	Direct evaluation of reflector effects on radiant flux from InGaN-based light-emitting diodes. Applied Optics, 2007, 46, 5974.	2.1	15
29	Optical polarization characteristics of light emission from sidewalls of primary-color light-emitting diodes. Semiconductor Science and Technology, 2008, 23, 072001.	2.0	13
30	Electroluminescent and Electrical Characteristics of Polar and Nonpolar InGaN/GaN Light-Emitting Diodes at Low Temperature. Japanese Journal of Applied Physics, 2006, 45, 7661-7666.	1.5	11
31	Equivalent-Circuit Analysis for the Electroluminescence-Efficiency Problem of InGaN/GaN Light-Emitting Diodes. Japanese Journal of Applied Physics, 2008, 47, 2112.	1.5	11
32	Experimental technique to correlate optical excitation intensities with electrical excitation intensities for semiconductor optoelectronic device characterization. Semiconductor Science and Technology, 2008, 23, 085018.	2.0	11
33	Analytical light-ray tracing in two-dimensional objects for light-extraction problems in light-emitting diodes. Applied Optics, 2008, 47, 88.	2.1	10
34	Radiative Recombination Efficiency of InGaN-Based Light-Emitting Diodes Evaluated at Various Temperatures and Injection Currents. Japanese Journal of Applied Physics, 2007, 46, L627-L629.	1.5	9
35	Recent progress in nonpolar LEDs as polarized light emitters. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 203-205.	1.8	9
36	Optimized doping and contact scheme for low-voltage 275-nm deep ultraviolet LEDs. Journal of Electronic Materials, 2006, 35, 750-753.	2.2	8

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37	Enhancement of external quantum efficiency in GaN-based light emitting diodes using a suspended geometry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 2216-2218.	0.8	8
38	Electrical Characteristics of Nonpolar InGaN-Based Light-Emitting Diodes Evaluated at Low Temperature. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 7309.	1.5	4
39	Nonpolar and Semipolar Orientations: Material Growth and Properties. <i>Materials Science Forum</i> , 0, 590, 211-232.	0.3	3
40	Effects of Growth Temperature and Postgrowth Annealing on Inhomogeneous Luminescence Characteristics of Green-Emitting InGaN Films. <i>Journal of Electronic Materials</i> , 2010, 39, 15-20.	2.2	3
41	Spontaneous formation of $\{1,0\}$ InGaN quantum wells on a $\{1,1,2\}$ GaN template and their electroluminescence characteristics. <i>Semiconductor Science and Technology</i> , 2010, 25, 015003.	2.0	3
42	A semipolar (10-1-3) InGaN/GaN green light emitting diode. <i>Materials Research Society Symposia Proceedings</i> , 2005, 892, 418.	0.1	1
43	Customized Filter Cube in Fluorescence Microscope Measurements of InGaN/GaN Quantum-Well Characterization. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 098003.	1.5	1
44	63.4: <i>Invited Paper</i> : Development and Application Prospects of InGaN-based Optoelectronic Devices Prepared in Nonpolar Orientations. <i>Digest of Technical Papers SID International Symposium</i> , 2008, 39, 969-971.	0.3	0